

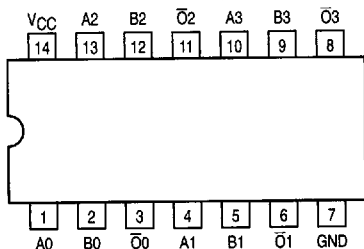
Low-Voltage CMOS Quad 2-Input NAND Gate With 5V-Tolerant Inputs

The MC74LCX00 is a high performance, quad 2-input NAND gate operating from a 2.7 to 3.6V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5V allows MC74LCX00 inputs to be safely driven from 5V devices.

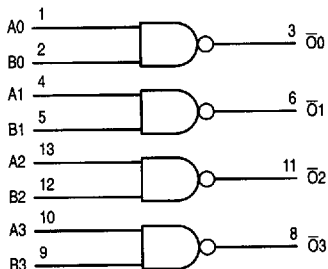
Current drive capability is 24mA at the outputs.

- Designed for 2.7 to 3.6V V_{CC} Operation
- 5V Tolerant Inputs — Interface Capability With 5V TTL Logic
- LVTTTL Compatible
- LVC MOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 μ A) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V

Pinout: 14-Lead (Top View)



LOGIC DIAGRAM



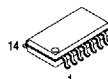
MC74LCX00

LCX

**LOW-VOLTAGE CMOS
QUAD 2-INPUT NAND GATE**



D SUFFIX
PLASTIC SOIC
CASE 751A-03



M SUFFIX
PLASTIC SOIC EIAJ
CASE 965-01



SD SUFFIX
PLASTIC SSOP
CASE 940A-03



DT SUFFIX
PLASTIC TSSOP
CASE 948G-01

PIN NAMES

Pins	Function
An, Bn	Data Inputs
On	Outputs

FUNCTION TABLE

Inputs		Outputs
An	Bn	On
L	L	H
L	H	H
H	L	H
H	H	L



ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0		V
V_I	DC Input Voltage	$-0.5 \leq V_I \leq +7.0$		V
V_O	DC Output Voltage	$-0.5 \leq V_O \leq V_{CC} + 0.5$	Note 1.	V
I_{IK}	DC Input Diode Current	-50	$V_I < GND$	mA
I_{OK}	DC Output Diode Current	-50	$V_O < GND$	mA
		+50	$V_O > V_{CC}$	mA
I_O	DC Output Source/Sink Current	± 50		mA
I_{CC}	DC Supply Current Per Supply Pin	± 100		mA
I_{GND}	DC Ground Current Per Ground Pin	± 100		mA
T_{STG}	Storage Temperature Range	-65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. Output in HIGH or LOW State. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
V_{CC}	Supply Voltage	2.0	3.3	3.6	V
	Operating Data Retention Only	1.5	3.3	3.6	
V_I	Input Voltage	0		5.5	V
V_O	Output Voltage (HIGH or LOW State)	0		V_{CC}	V
I_{OH}	HIGH Level Output Current, $V_{CC} = 3.0V - 3.6V$			-24	mA
I_{OL}	LOW Level Output Current, $V_{CC} = 3.0V - 3.6V$			24	mA
I_{OH}	HIGH Level Output Current, $V_{CC} = 2.7V - 3.0V$			-12	mA
I_{OL}	LOW Level Output Current, $V_{CC} = 2.7V - 3.0V$			12	mA
T_A	Operating Free-Air Temperature	-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8V to 2.0V, $V_{CC} = 3.0V$	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic	Condition	$T_A = -40^\circ\text{C to } +85^\circ\text{C}$		Unit
			Min	Max	
V_{IH}	HIGH Level Input Voltage (Note 2.)	$2.7V \leq V_{CC} \leq 3.6V$	2.0		V
V_{IL}	LOW Level Input Voltage (Note 2.)	$2.7V \leq V_{CC} \leq 3.6V$		0.8	V
V_{OH}	HIGH Level Output Voltage	$2.7V \leq V_{CC} \leq 3.6V$; $I_{OH} = -100\mu A$	$V_{CC} - 0.2$		V
		$V_{CC} = 2.7V$; $I_{OH} = -12mA$	2.2		
		$V_{CC} = 3.0V$; $I_{OH} = -18mA$	2.4		
		$V_{CC} = 3.0V$; $I_{OH} = -24mA$	2.2		
V_{OL}	LOW Level Output Voltage	$2.7V \leq V_{CC} \leq 3.6V$; $I_{OL} = 100\mu A$		0.2	V
		$V_{CC} = 2.7V$; $I_{OL} = 12mA$		0.4	
		$V_{CC} = 3.0V$; $I_{OL} = 16mA$		0.4	
		$V_{CC} = 3.0V$; $I_{OL} = 24mA$		0.55	

2. These values of V_I are used to test DC electrical characteristics only.

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DC ELECTRICAL CHARACTERISTICS (continued)

Symbol	Characteristic	Condition	T _A = -40°C to +85°C		Unit
			Min	Max	
I _I	Input Leakage Current	2.7V ≤ V _{CC} ≤ 3.6V; 0V ≤ V _I ≤ 5.5V		±5.0	μA
I _{CC}	Quiescent Supply Current	2.7 ≤ V _{CC} ≤ 3.6V; V _I = GND or V _{CC}		10	μA
		2.7 ≤ V _{CC} ≤ 3.6V; 3.6 ≤ V _I ≤ 5.5V		±10	μA
ΔI _{CC}	Increase in I _{CC} per Input	2.7 ≤ V _{CC} ≤ 3.6V; V _{IH} = V _{CC} - 0.6V		500	μA

AC CHARACTERISTICS (t_R = t_F = 2.5ns; C_L = 50pF; R_L = 500Ω)

Symbol	Parameter	Waveform	Limits			Unit
			T _A = -40°C to +85°C			
			V _{CC} = 3.0V to 3.6V		V _{CC} = 2.7V	
			Min	Max	Max	
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	1.5 1.5	5.2 5.2	6.0 6.0	ns
t _{OSSL} t _{OSLH}	Output-to-Output Skew (Note 3.)			1.0 1.0		ns

3. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSSL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

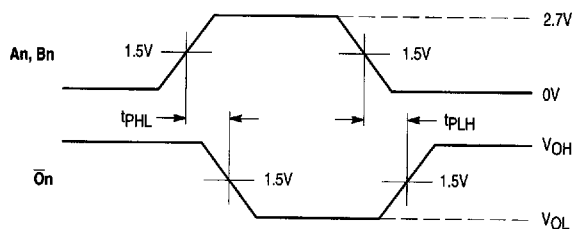
DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	T _A = +25°C			Unit
			Min	Typ	Max	
V _{OLP}	Dynamic LOW Peak Voltage (Note 4.)	V _{CC} = 3.3V, C _L = 50pF, V _{IH} = 3.3V, V _{IL} = 0V		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 4.)	V _{CC} = 3.3V, C _L = 50pF, V _{IH} = 3.3V, V _{IL} = 0V		0.8		V

4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

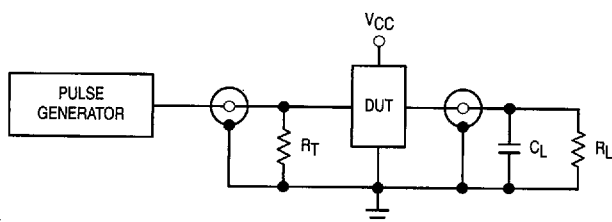
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V _{CC} = 3.3V, V _I = 0V or V _{CC}	7	pF
C _{OUT}	Output Capacitance	V _{CC} = 3.3V, V _I = 0V or V _{CC}	8	pF
CPD	Power Dissipation Capacitance	10MHz, V _{CC} = 3.3V, V _I = 0V or V _{CC}	25	pF



PROPAGATION DELAYS
 $t_R = t_F = 2.5\text{ns}$, 10% to 90%; $f = 1\text{MHz}$; $t_W = 500\text{ns}$

Figure 1. AC Waveforms



$C_L = 50\text{pF}$ or equivalent (Includes jig and probe capacitance)
 $R_L = R_1 = 500\Omega$ or equivalent
 $R_T = Z_{OUT}$ of pulse generator (typically 50Ω)

Figure 2. Test Circuit